

ABSTRACT OF THE DISCLOSURE

The nonvolatile semiconductor memory device has a floating gate electrode that is formed on the semiconductor region and stores carriers injected from the semiconductor 5 region and a control gate electrode that controls the quantity of stored carriers by applying a predetermined voltage to the floating gate electrode. The source region is formed in the semiconductor region on one of side regions of the floating gate electrode and control gate electrode, while 10 the drain region is formed on the other of the side regions thereof. The drain region creates an electric field from which the carriers injected into the floating gate electrode are subject to an external force having an element directed from the semiconductor region to the floating gate electrode.

10003434.10003434